

**30V COMPLEMENTARY ENHANCEMENT MODE MOSFET**
**Product Summary**

Device	$V_{(BR)DSS}$	$R_{DS(ON) \max}$	Package	$I_{D \max}$ $T_A = +25^\circ\text{C}$
N-Channel	30V	20m $\Omega$ @ $V_{GS} = 10\text{V}$	SO-8	8.5A
		32m $\Omega$ @ $V_{GS} = 4.5\text{V}$		7.0A
P-Channel	-30V	45m $\Omega$ @ $V_{GS} = -10\text{V}$		-5.5A
		85m $\Omega$ @ $V_{GS} = -4.5\text{V}$		-4.1A

**Description**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

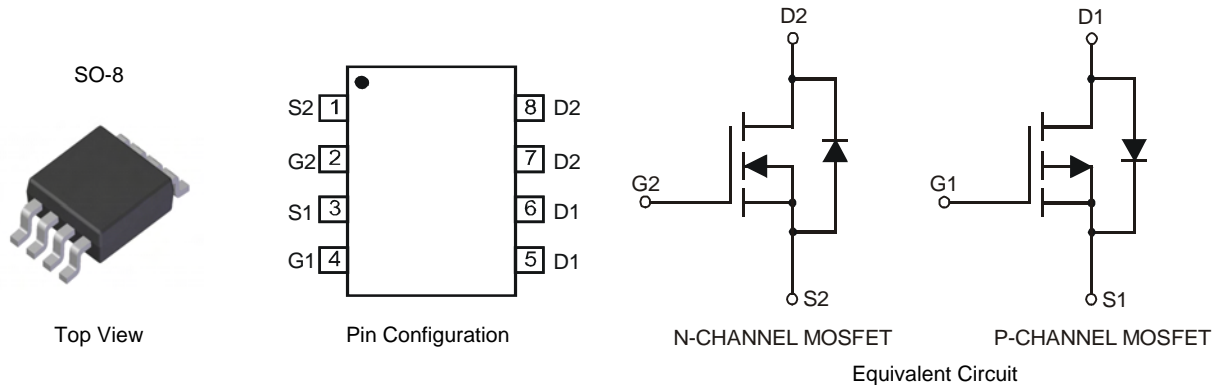
- DC Motor Control
- DC-AC Inverters

**Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

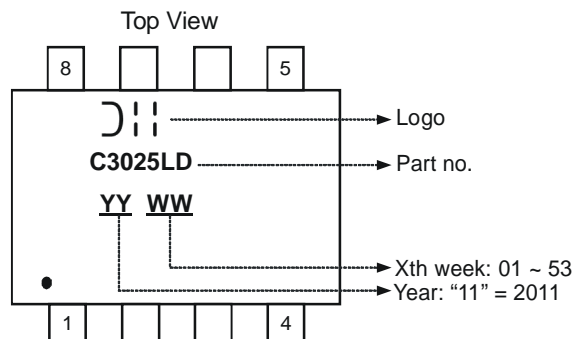
**Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)


**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMC3025LSD-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**


**Maximum Ratings N-CHANNEL** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	6.5	A
		T <sub>A</sub> = +70°C		5.1	A
	t<10s	T <sub>A</sub> = +25°C	I <sub>D</sub>	8.5	A
		T <sub>A</sub> = +70°C		6.8	A
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	5.3	A
		T <sub>A</sub> = +70°C		4.1	A
	t<10s	T <sub>A</sub> = +25°C	I <sub>D</sub>	7.0	A
		T <sub>A</sub> = +70°C		5.5	A
Maximum Continuous Body Diode Forward Current (Note 5)			I <sub>S</sub>	2	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	60	A

**Maximum Ratings P-CHANNEL** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-4.2	A
		T <sub>A</sub> = +70°C		-3.2	A
	t<10s	T <sub>A</sub> = +25°C	I <sub>D</sub>	-5.5	A
		T <sub>A</sub> = +70°C		-4.3	A
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-3.5	A
		T <sub>A</sub> = +70°C		-2.3	A
	t<10s	T <sub>A</sub> = +25°C	I <sub>D</sub>	-4.1	A
		T <sub>A</sub> = +70°C		-3.2	A
Maximum Continuous Body Diode Forward Current (Note 5)			I <sub>S</sub>	-2	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	-30	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.2	W
	T <sub>A</sub> = +70°C		0.77	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	104	°C/W
	t<10s		62	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.5	W
	T <sub>A</sub> = +70°C		0.95	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	83	°C/W
	t<10s		49	
Thermal Resistance, Junction to Case (Note 5)		R <sub>θJC</sub>	15	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.  
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

**Electrical Characteristics N-CHANNEL** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±1	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	15	20	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7.4A
		—	23	32		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6A
Forward Transfer Admittance	Y <sub>fs</sub>	—	8	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 10A
Diode Forward Voltage	V <sub>SD</sub>	—	0.70	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	501	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	72	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	57	—		
Gate resistance	R <sub>g</sub>	—	1.84	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	4.6	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 10A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	9.8	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.6	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.0	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	3.9	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>r</sub>	—	4.2	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	16.6	—		
Turn-Off Fall Time	t <sub>f</sub>	—	5.8	—		
Reverse Recovery Time	t <sub>rr</sub>	—	5.5	—	ns	I <sub>F</sub> = 12A, di/dt = 500A/μs
Reverse Recovery Charge	Q <sub>rr</sub>	—	2.6	—	nC	

**Electrical Characteristics P-CHANNEL** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—	-2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	38	45	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5.2A
		—	65	85		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A
Forward Transfer Admittance	Y <sub>fs</sub>	—	5	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -5.2A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	590	—	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	69	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	53	—	pF	
Gate resistance	R <sub>g</sub>	—	11	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.1	—	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -6A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	10.5	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	1.9	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	6.8	—	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>r</sub>	—	4.9	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	28.4	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	12.4	—	ns	
Reverse Recovery Time	t <sub>rr</sub>	—	14	—	ns	I <sub>F</sub> = 12A, di/dt = 500A/μs
Reverse Recovery Charge	Q <sub>rr</sub>	—	11	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

**N-CHANNEL**

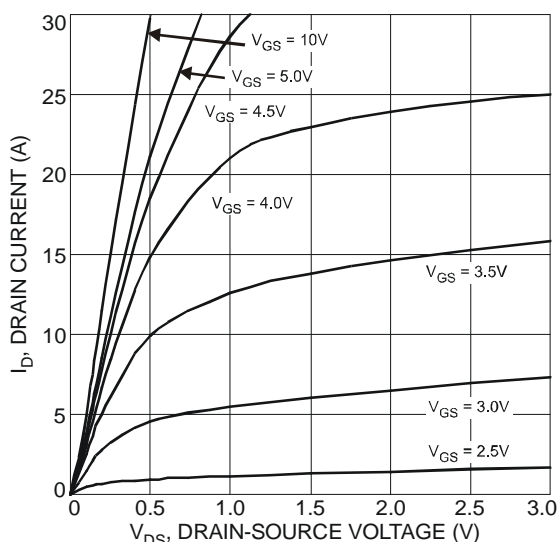


Figure 1. Typical Output Characteristic

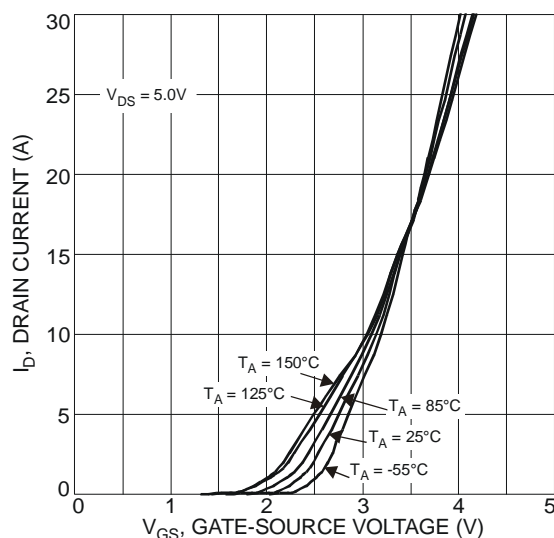


Figure 2. Typical Transfer Characteristics

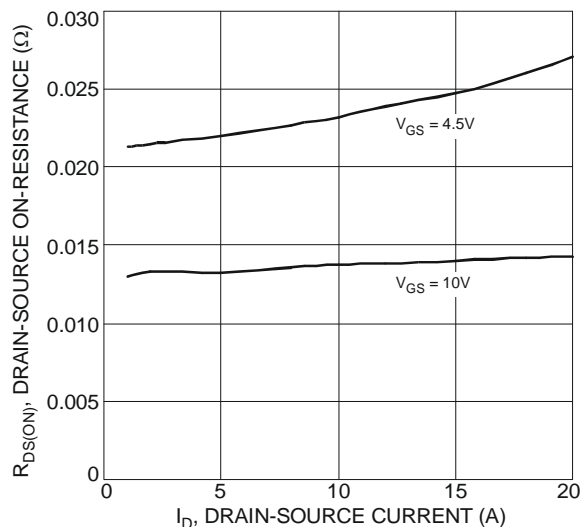


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

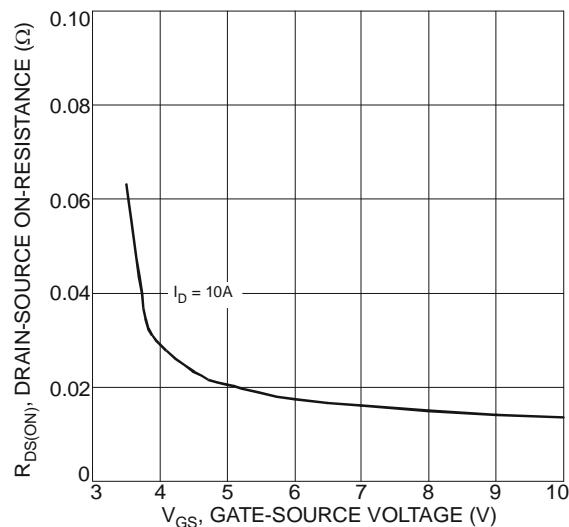


Figure 4. Typical On-Resistance vs. Drain Current and Gate Voltage

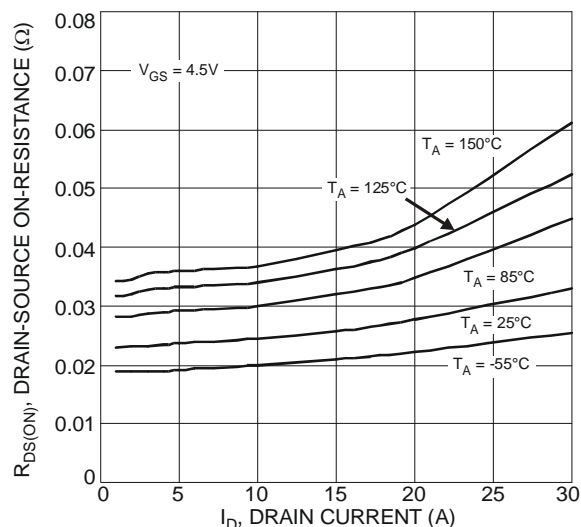


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

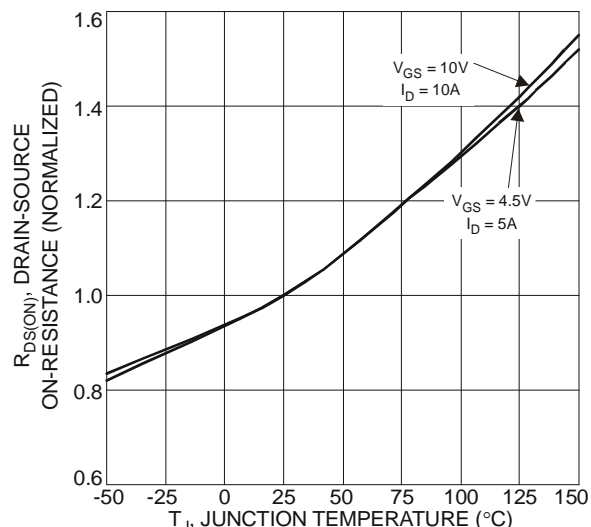


Figure 6. On-Resistance Variation with Temperature

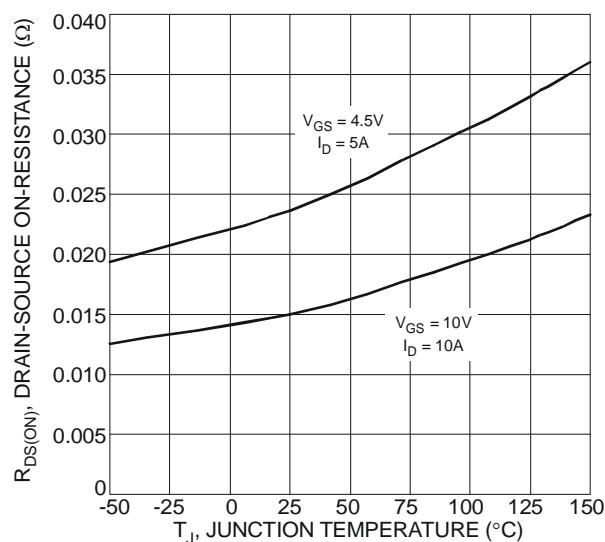


Figure 7. On-Resistance Variation with Temperature

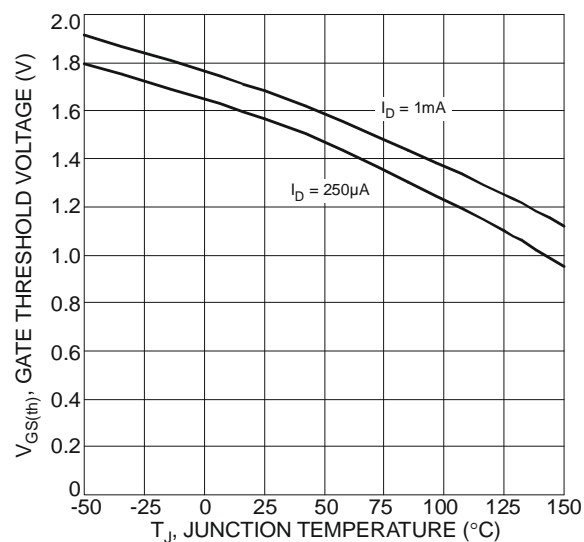


Figure 8. Gate Threshold Variation vs. Ambient Temperature

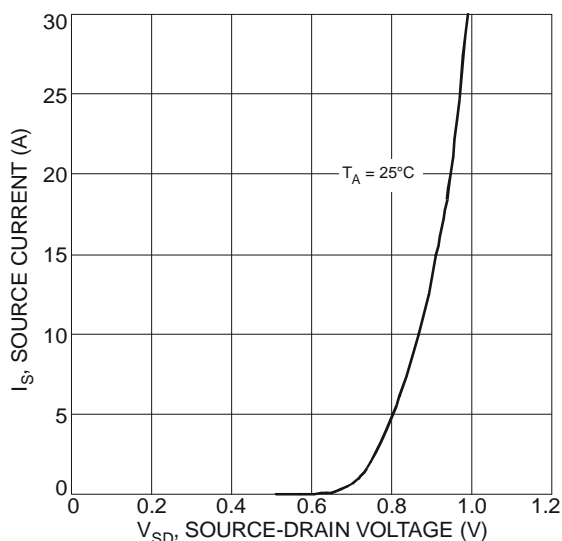


Figure 9. Diode Forward Voltage vs. Current

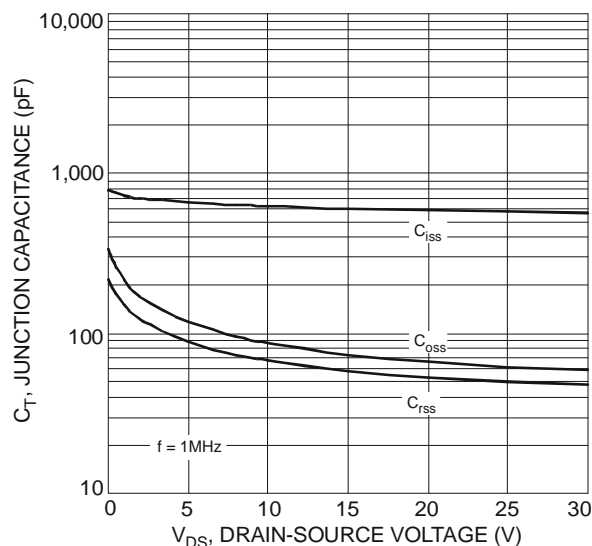


Figure 10. Typical Junction Capacitance

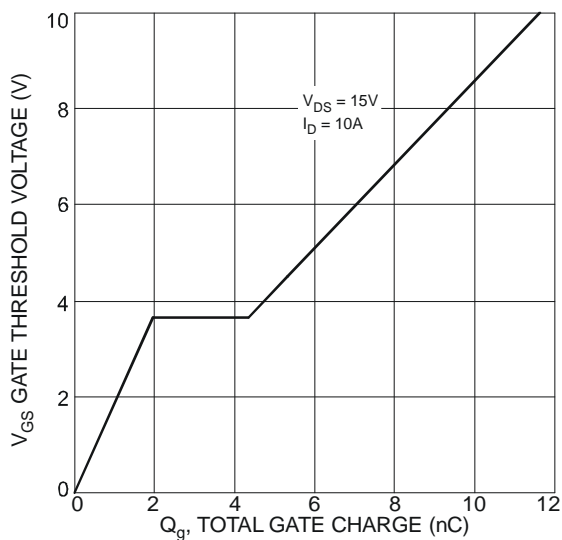


Figure 11. Gate Charge

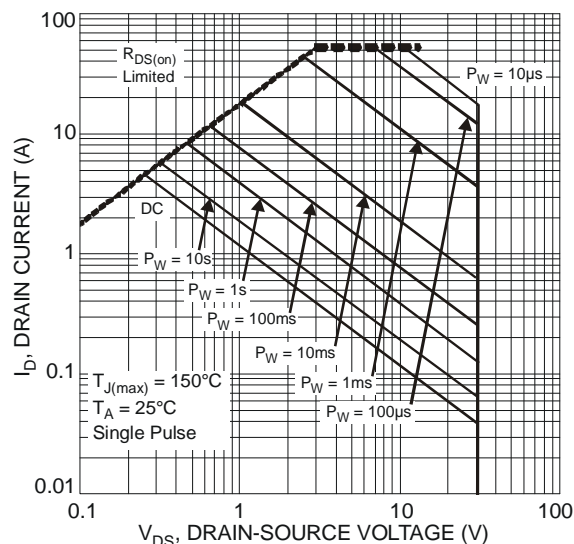


Figure 12. SOA, Safe Operation Area

**P-CHANNEL**

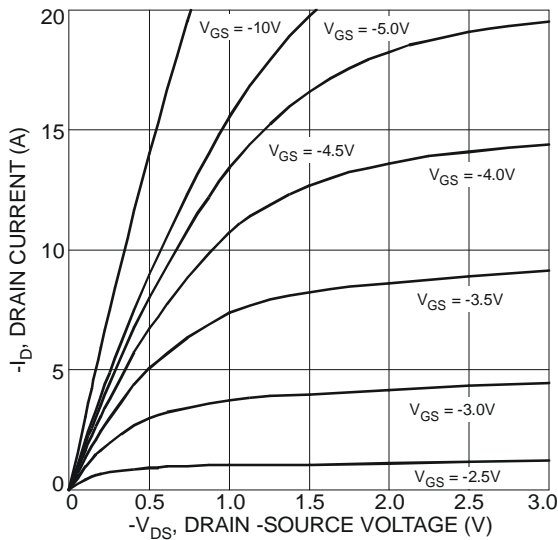


Figure 13. Typical Output Characteristics

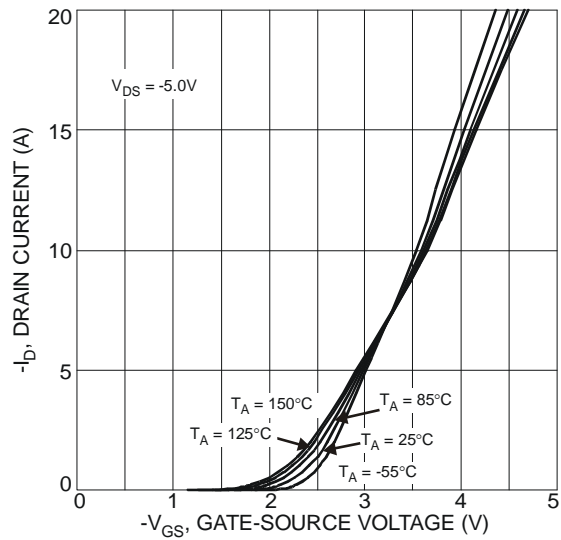


Figure 14. Typical Transfer Characteristics

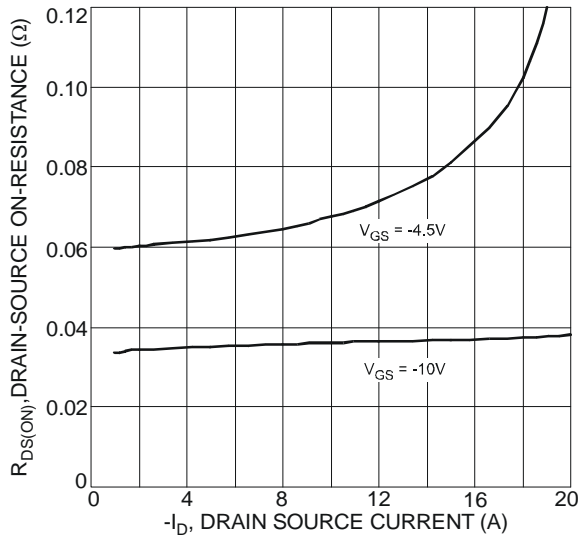


Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

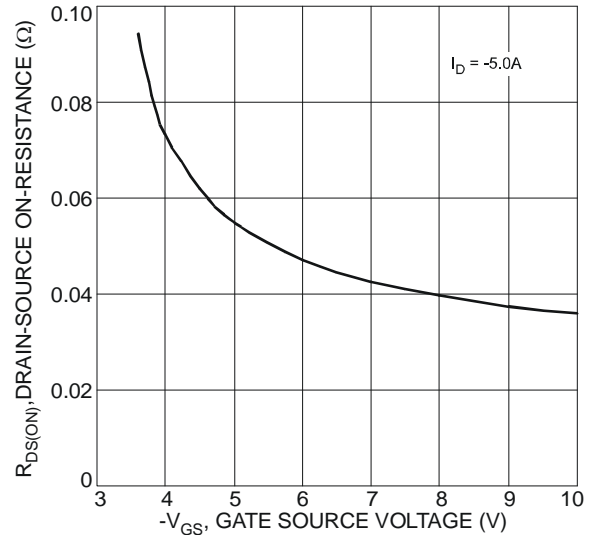


Figure 16. Typical On-Resistance vs. Drain Current and Gate Voltage

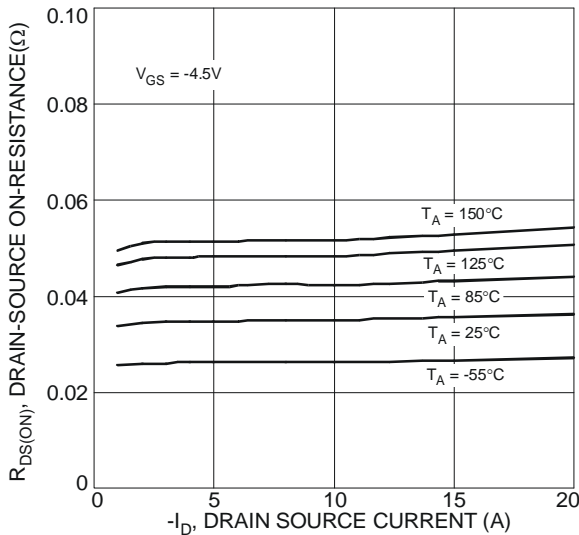


Figure 17. Typical On-Resistance vs. Drain Current and Temperature

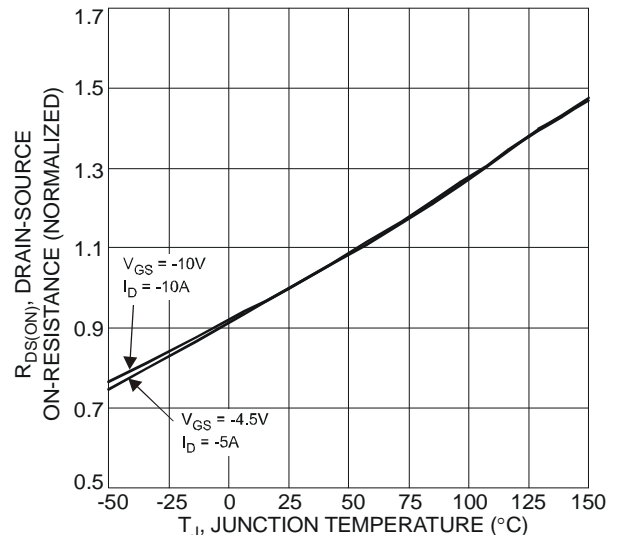


Figure 18. On-Resistance Variation with Temperature

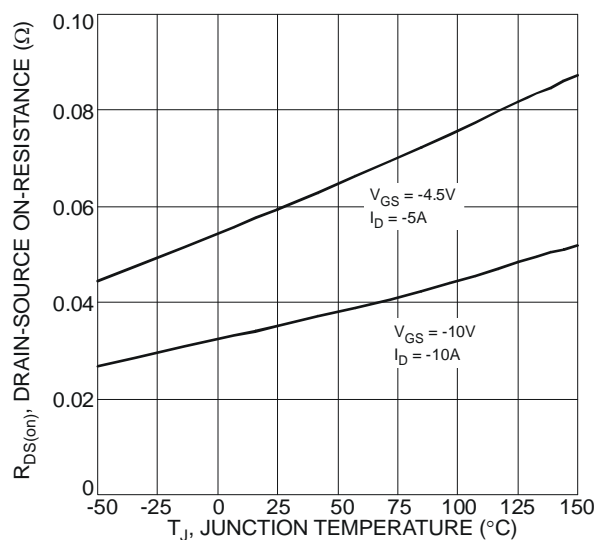


Figure 19. On-Resistance Variation with Temperature

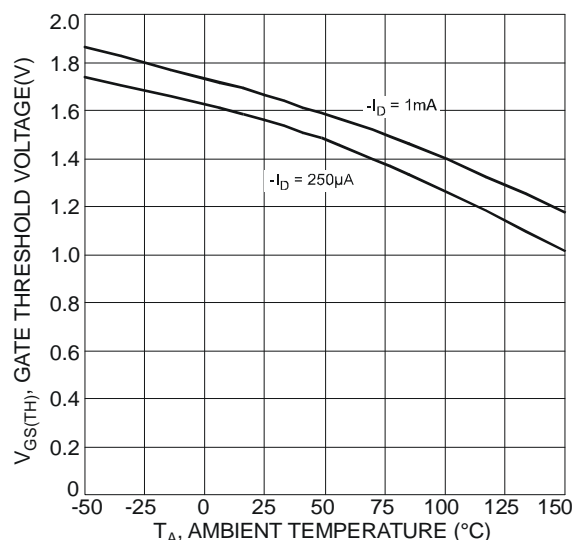


Figure 20. Gate Threshold Variation vs. Ambient Temperature

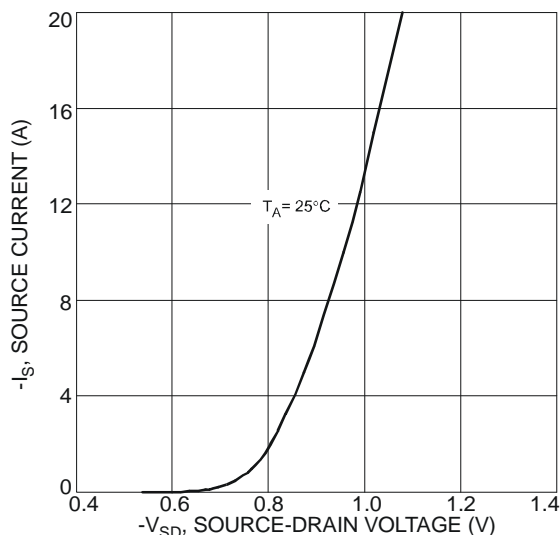


Figure 21. Diode Forward Voltage vs. Current

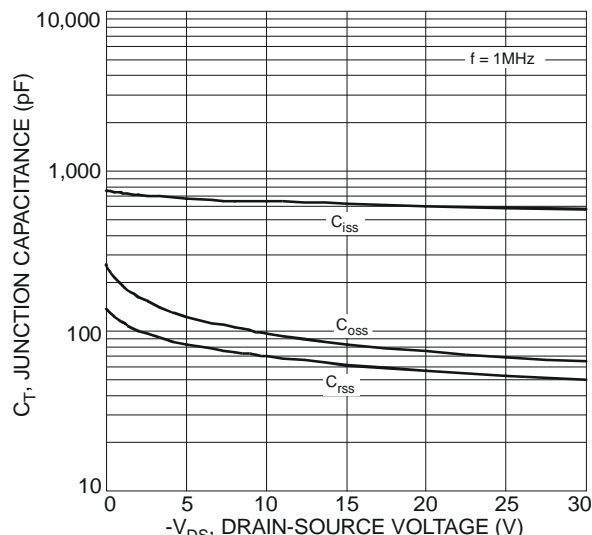


Figure 22. Typical Junction Capacitance

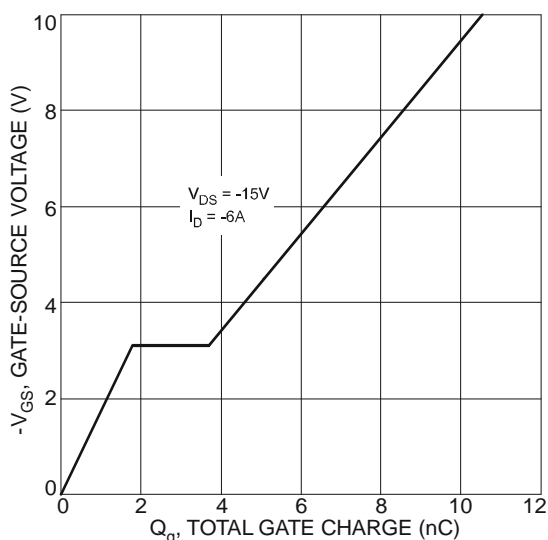


Figure 23. Gate-Charge Characteristics

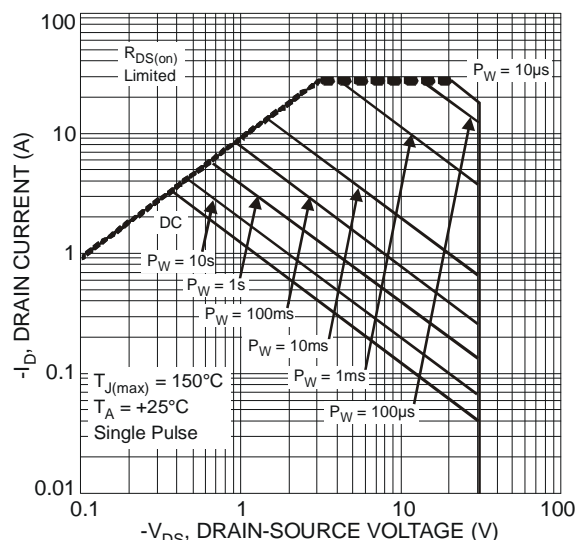
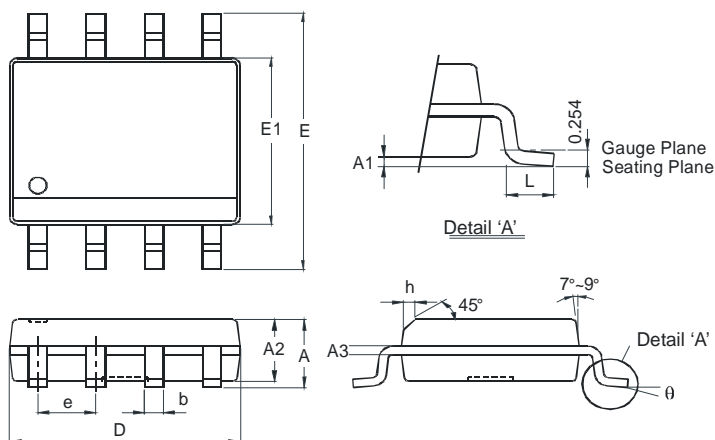


Figure 24. SOA, Safe Operation Area

## Package Outline Dimensions

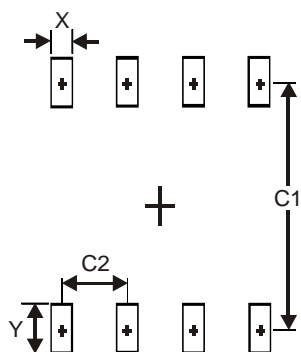
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27



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